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(12) **United States Design Patent**
Muehlensiep et al.

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(54) **POWER SEMICONDUCTOR MODULE**

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(**) Term: **14 Years**

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(52) **U.S. Cl.**
USPC **D13/182**

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CPC . H01L 21/00; H01L 2224/42; H01L 2224/43; H01L 2021/00; H01L 2021/02; H01L 2021/04; H01L 21/4814; H01L 21/4846; H01L 21/4871; H01L 21/47144; H01L 23/12; H01L 23/13; H01L 23/14; H01L 23/147; H01L 2924/171; H01L 2924/1711; H01L 2924/1715; H01L 2924/17151; H01L 2924/181; H01L 2924/1811; H01L 2924/1815; H01L 2924/19042; H01L 2924/1905; H01L 224/08054; H01L 23/58; H05B 41/14; H02B 6/4201; G02B 6/4256; G02B 6/4257; G02B 6/4261; G02B 6/4262; G02B 6/428; G02B 6/4281; H05K 1/14; H05K 1/141; H05K 1/142; H05K 1/144; H05K 1/18; H05K 1/181; H05K 1/182; H05K 1/026
See application file for complete search history.

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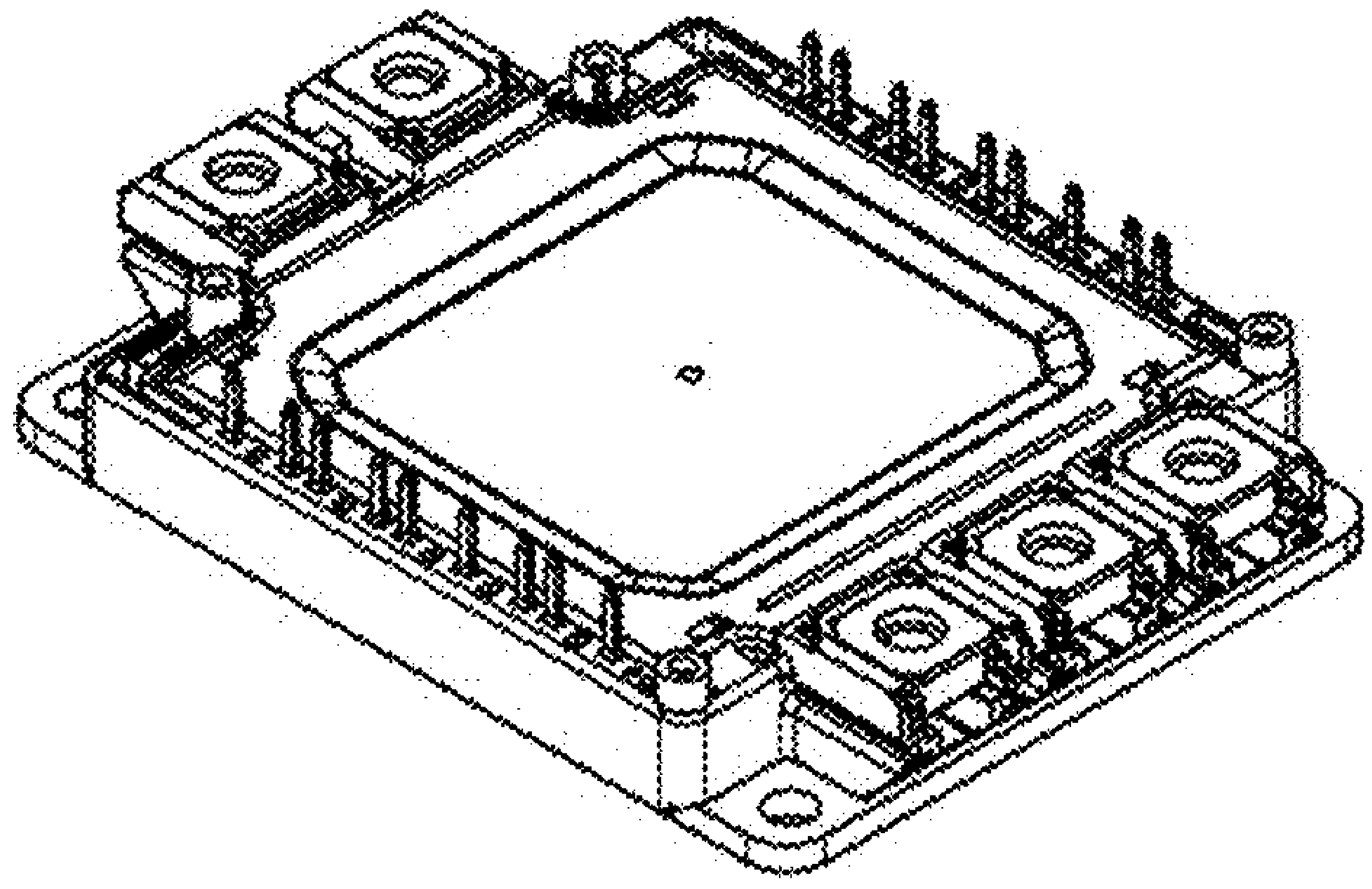
(57) **CLAIM**

The ornamental design for a power semiconductor module, as shown and described.

DESCRIPTION

FIG. **1** is a top, side perspective view of a power semiconductor module, showing our new design;
FIG. **2** is a front elevation view thereof;
FIG. **3** is a top plan view thereof;
FIG. **4** is rear elevation view thereof; and,
FIG. **5** is a side elevation view thereof.
All surfaces not shown form no part of the claimed design.

1 Claim, 5 Drawing Sheets



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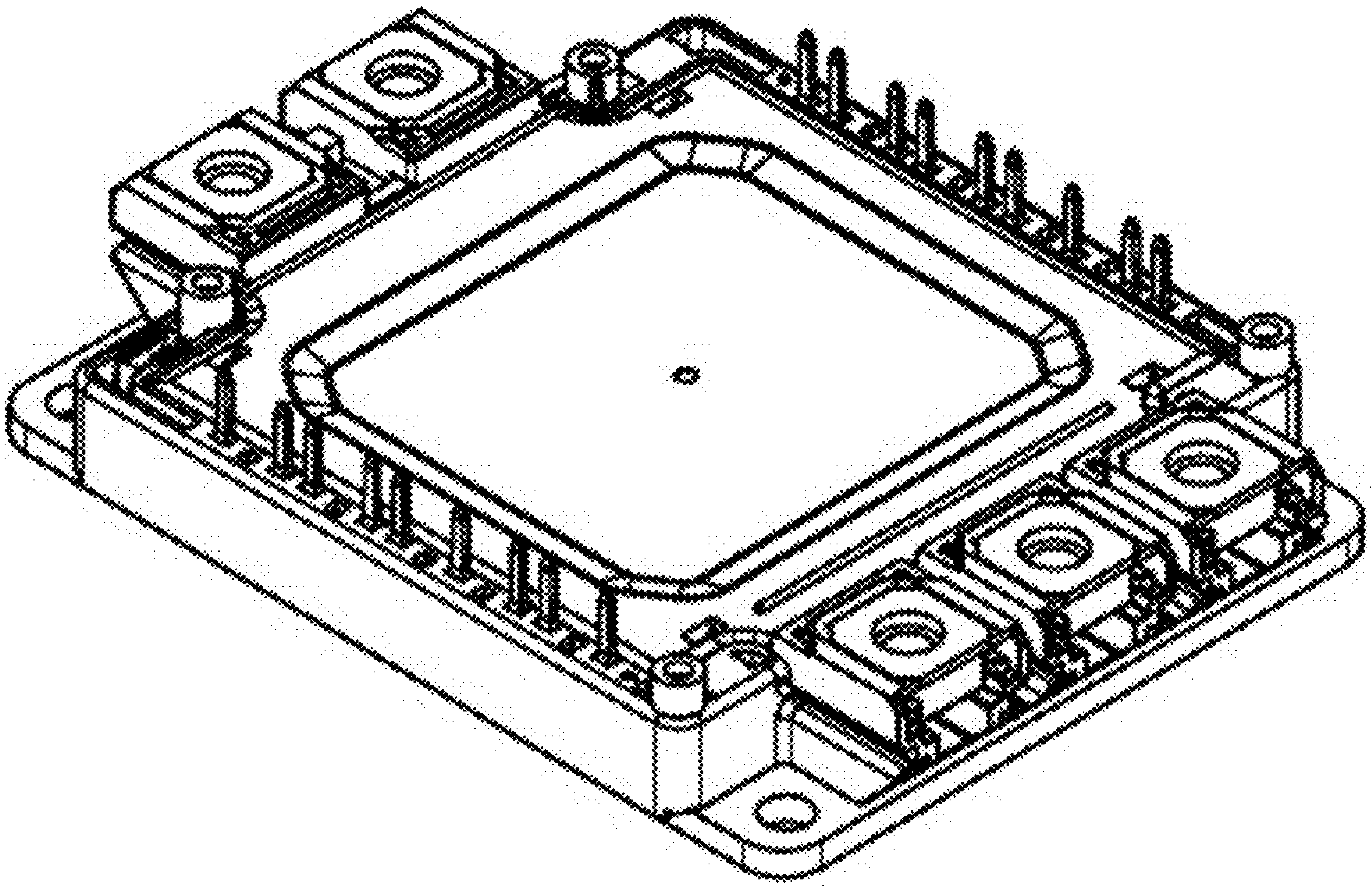

FIG. 1

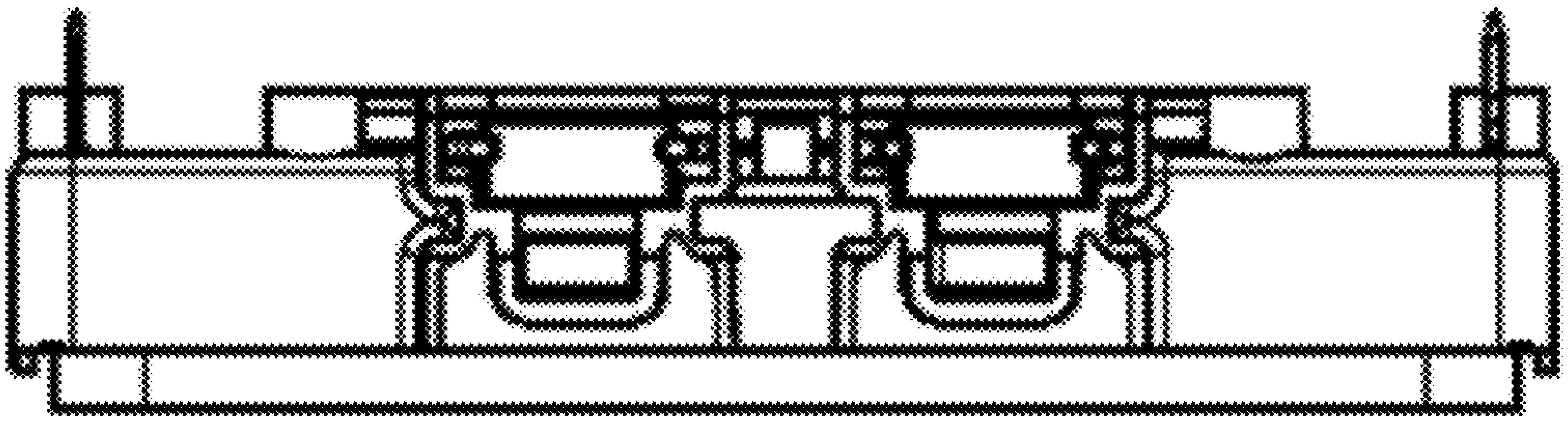

FIG. 2

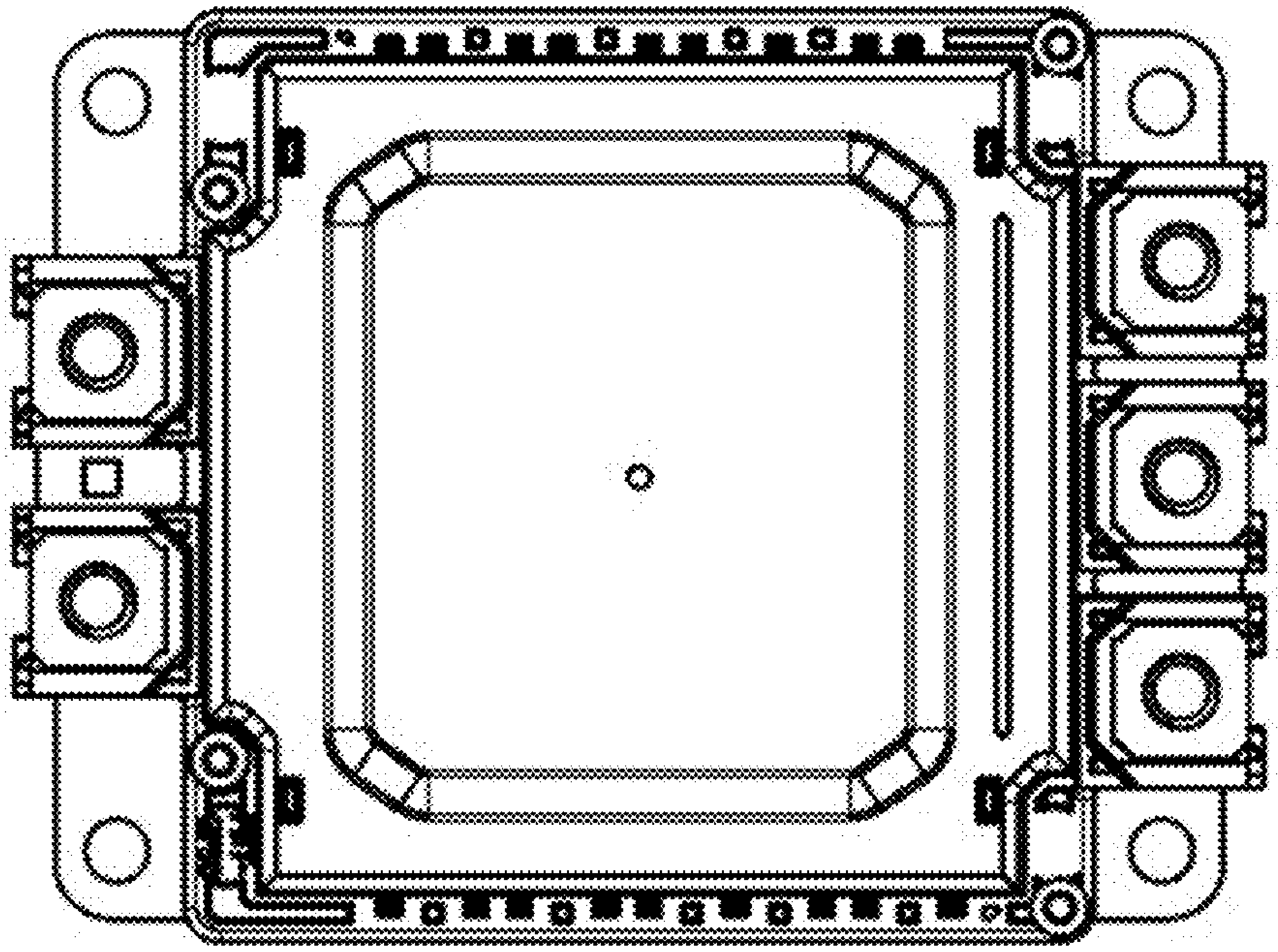

FIG. 3

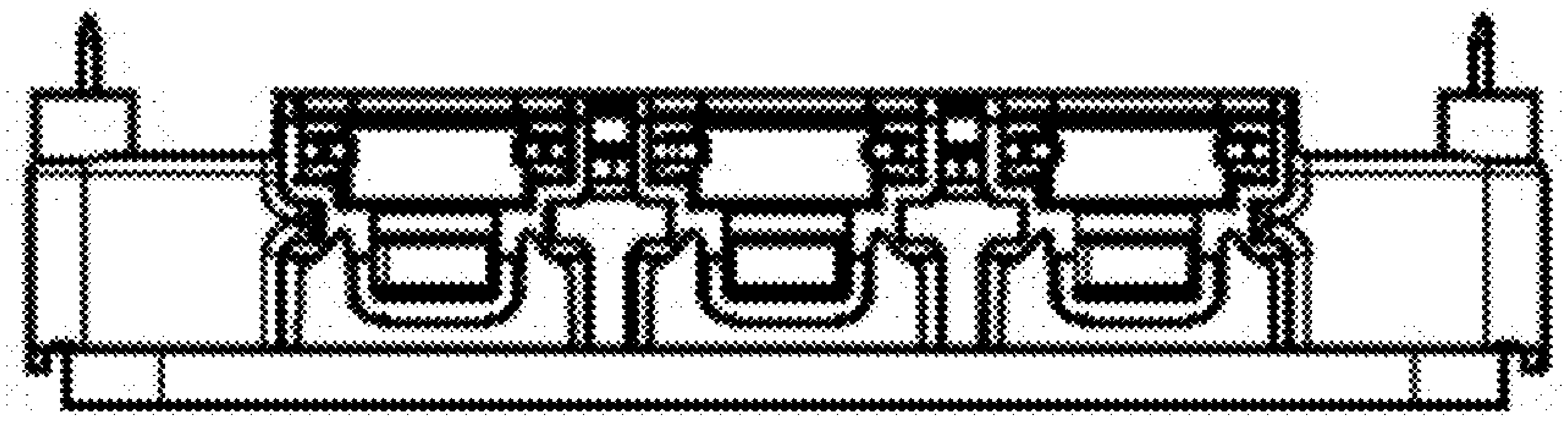

FIG. 4

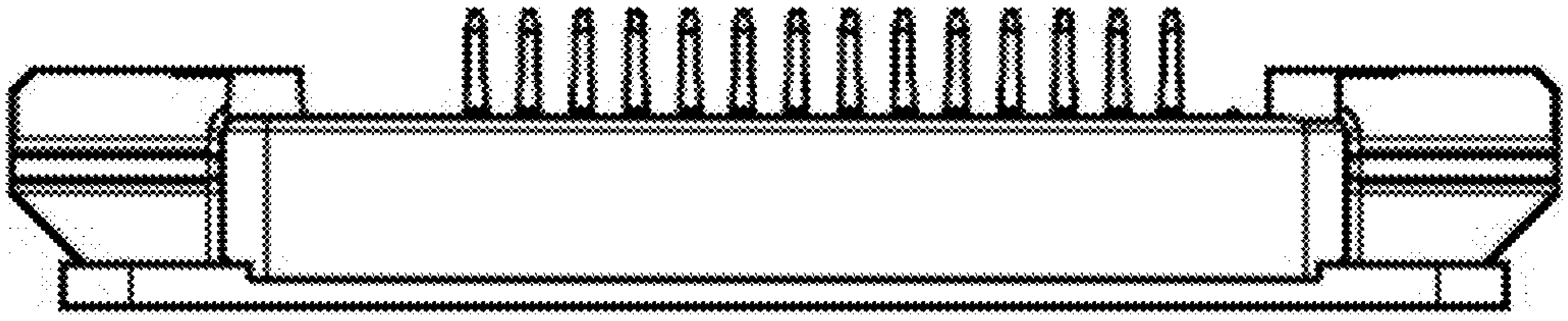

FIG. 5